NSN 5961-00-335-8934

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-335-8934 **Inclosure Material:** Glass **Overall Length:** Between 0.150 inches and 0.170 inches **Terminal Length:** 1.000 inches **Overall Diameter:** Between 0.068 inches and 0.076 inches **Mounting Method:** Terminal **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 20.0 breakdown voltage, dc and 16.0 working peak reverse voltage **Current Rating Per Characteristic:** 150.00 nanoamperes forward current, average peak **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector preset **Capacitance Rating In Picofarads:** 1.2 **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/445 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No